

CLL3595

**SURFACE MOUNT
LOW LEAKAGE SILICON DIODE**



SOD-80 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CLL3595 type is an epitaxial planar silicon diode, manufactured in a hermetically sealed glass surface mount package, designed for low leakage, high conductance applications.

MARKING: CATHODE BAND

MAXIMUM RATINGS: ($T_A=25^{\circ}\text{C}$)

Peak Repetitive Reverse Voltage
Peak Working Reverse Voltage
Average Forward Current
Forward Steady-State Current
Recurrent Peak Forward Current
Peak Forward Surge Current (1.0s pulse)
Peak Forward Surge Current (1.0 μ s pulse)
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL

V_{RRM} 150
 V_{RWM} 125
 I_O 150
 I_F 225
 I_f 600
 I_{FSM} 500
 I_{FSM} 4.0
 P_D 500
 T_J, T_{stg} -65 to +200
 Θ_{JA} 350

UNITS

V
V
mA
mA
mA
mA
A
mW
 $^{\circ}\text{C}$
 $^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

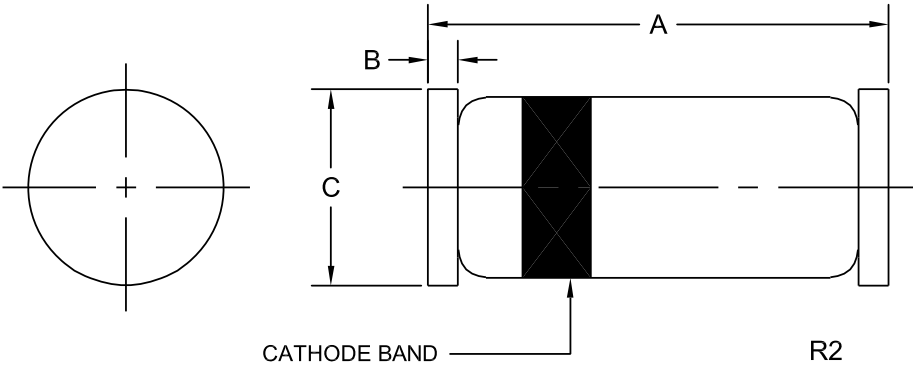
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_R	$V_R=125\text{V}$		1.0	nA
I_R	$V_R=125\text{V}, T_A=125^{\circ}\text{C}$		500	nA
I_R	$V_R=125\text{V}, T_A=150^{\circ}\text{C}$		3.0	μA
I_R	$V_R=30\text{V}, T_A=125^{\circ}\text{C}$		300	nA
BV_R	$I_R=100\mu\text{A}$	150		V
V_F	$I_F=1.0\text{mA}$	0.54	0.69	V
V_F	$I_F=5.0\text{mA}$	0.62	0.77	V
V_F	$I_F=10\text{mA}$	0.65	0.80	V
V_F	$I_F=50\text{mA}$	0.75	0.88	V
V_F	$I_F=100\text{mA}$	0.79	0.92	V
V_F	$I_F=200\text{mA}$	0.834	1.00	V
C_T	$V_R=0, f=1.0\text{MHz}$		8.0	pF
t_{rr}	$V_R=3.5\text{V}, I_F=10\text{mA}, R_L=1.0\text{k}\Omega$		3.0	μs

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SOD-80 CASE - MECHANICAL OUTLINE



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DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.130	0.146	3.30	3.71
B	0.014		0.35	
C (DIA)	0.049	0.067	1.25	1.70

SOD-80 (REV:R2)

R4 (8-January 2010)